

100mA 30V(0.28mm)

[Go to Home Page](#)

Chip Information

Chip Size	0.28 x 0.28mm
Pad Size	0.16 x 0.16mm
Chip Quantity	141234 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	30	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	30	V	
Average Forward Rectified Current	IF(AV)	100	mA	
Peak Forward Surge Current	IFSM	0.6	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.370	0.345	0.320	V	IF=1mA Ta=25degC
	VF2	0.450	0.438	0.396	V	IF=10mA Ta=25degC
	VF3	0.550	0.540	0.465	V	IF=30mA Ta=25degC
	VF4	1.000	0.990	0.710	V	IF=100mA Ta=25degC
	VF5				V	
Maximum DC Reverse Current	IR1	0.5	0.4	0.08	uA	VR=25V Ta=25degC
	IR2	0.5	0.1	0.02	uA	VR=10V Ta=25degC
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	30	35	50	V	IR=100uA
Junction Capacitance	Cj			7	pF	V=0V,f=1MHz
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
XFC025	180 +/- 20um	Au(For Eutectic)
XFC027	150 +/- 20um	Au(For Eutectic)
XFC028	95 +/- 15um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For RB520G-30